



FQB6N90 / FQI6N90

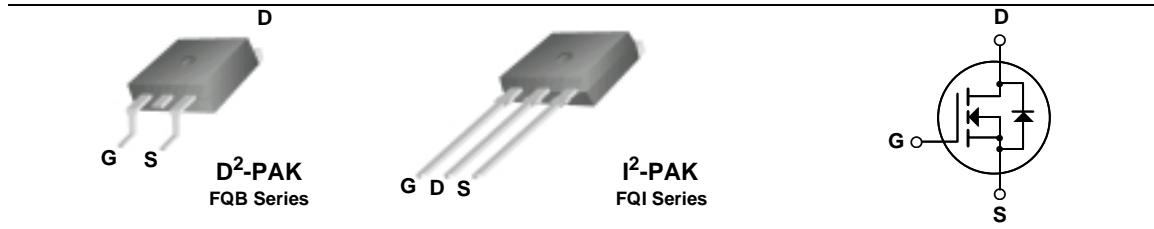
900V N-Channel MOSFET

General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology is especially tailored to minimize on-state resistance, provide superior switching performance, and withstand a high energy pulse in the avalanche and commutation modes. These devices are well suited for high efficiency switch mode power supplies.

Features

- 5.8A, 900V, $R_{DS(on)} = 1.9\Omega$ @ $V_{GS} = 10$ V
- Low gate charge (typical 40 nC)
- Low C_{RSS} (typical 17 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQB6N90 / FQI6N90	Units
V_{DSS}	Drain-Source Voltage	900	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	5.8	A
	- Continuous ($T_C = 100^\circ\text{C}$)	3.7	A
I_{DM}	Drain Current - Pulsed	(Note 1)	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	mJ
I_{AR}	Avalanche Current	(Note 1)	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	3.13	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	167	W
	- Derate above 25°C	1.34	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.75	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	40	$^\circ\text{C}/\text{W}$
$R_{\theta CA}$	Thermal Resistance, Case-to-Ambient	--	62.5	$^\circ\text{C}/\text{W}$

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	900	--	--	V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	--	0.96	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 900 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$	--	--	10	μA
		$V_{\text{DS}} = 720 \text{ V}$, $T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{\text{GS}} = 30 \text{ V}$, $V_{\text{DS}} = 0 \text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{\text{GS}} = -30 \text{ V}$, $V_{\text{DS}} = 0 \text{ V}$	--	--	-100	nA

On Characteristics

$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_D = 250 \mu\text{A}$	3.0	--	5.0	V
$R_{\text{DS}(\text{on})}$	Static Drain-Source On-Resistance	$V_{\text{GS}} = 10 \text{ V}$, $I_D = 2.9 \text{ A}$	--	1.5	1.9	Ω
g_{FS}	Forward Transconductance	$V_{\text{DS}} = 50 \text{ V}$, $I_D = 2.9 \text{ A}$ (Note 4)	--	6.3	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{\text{DS}} = 25 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$, $f = 1.0 \text{ MHz}$	--	1440	1880	pF
C_{oss}	Output Capacitance		--	140	185	pF
C_{rss}	Reverse Transfer Capacitance		--	17	23	pF

Switching Characteristics

$t_{\text{d}(\text{on})}$	Turn-On Delay Time	$V_{\text{DD}} = 450 \text{ V}$, $I_D = 5.8 \text{ A}$, $R_G = 25 \Omega$	--	35	80	ns
t_r	Turn-On Rise Time		--	80	170	ns
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time		--	95	200	ns
t_f	Turn-Off Fall Time		--	55	120	ns
Q_g	Total Gate Charge	$V_{\text{DS}} = 720 \text{ V}$, $I_D = 5.8 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$	--	40	52	nC
Q_{gs}	Gate-Source Charge		--	8.5	--	nC
Q_{gd}	Gate-Drain Charge		--	20	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	5.8	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	23.2	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}$, $I_S = 5.8 \text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{\text{GS}} = 0 \text{ V}$, $I_S = 5.8 \text{ A}$, $dI_F / dt = 100 \text{ A}/\mu\text{s}$	--	400	--	ns
Q_{rr}	Reverse Recovery Charge		--	4.3	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 40\text{mH}$, $I_{AS} = 5.8\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 5.8\text{A}$, $dI/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq \text{BV}_{\text{DSS}}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

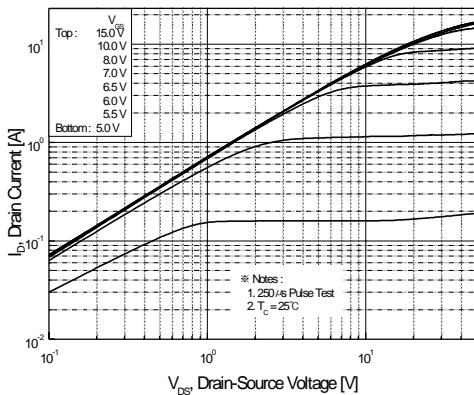


Figure 1. On-Region Characteristics

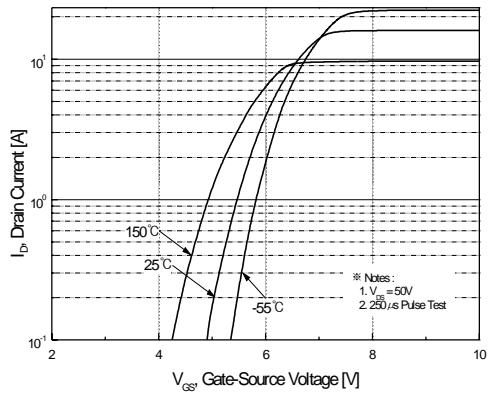


Figure 2. Transfer Characteristics

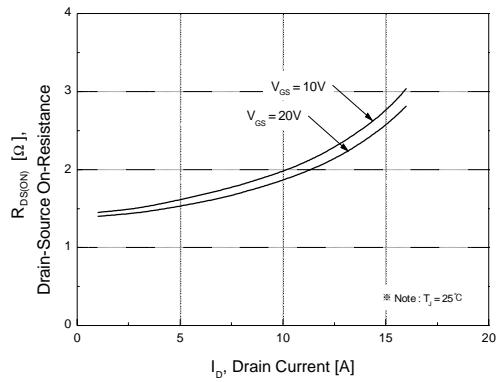


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

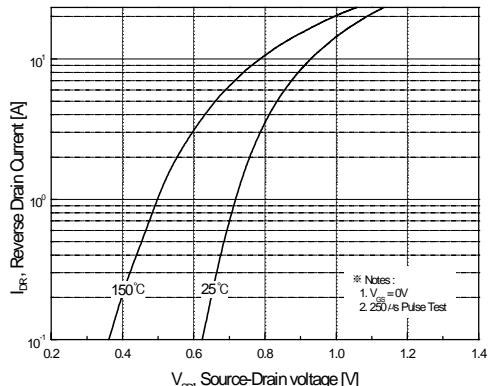


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

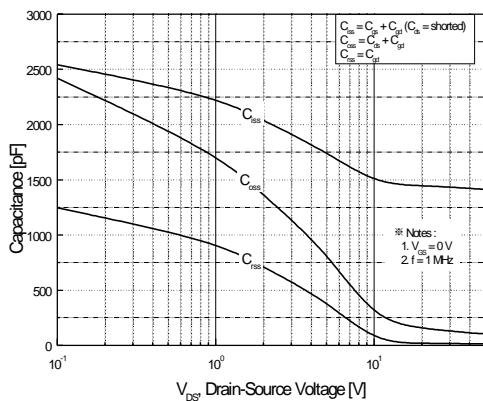


Figure 5. Capacitance Characteristics

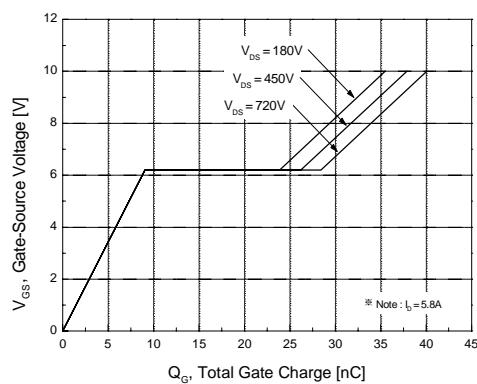


Figure 6. Gate Charge Characteristics